PNP/NPN Epitaxial Planar Silicon Transistor



2SB631,631K/2SD600,600K 100V/120V, 1A Low-Frequency Power Amplifier Applications

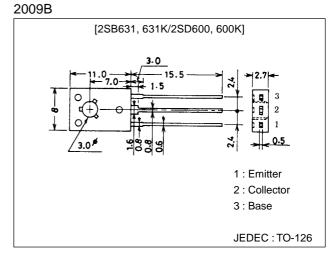
Features

 \cdot High breakdown voltage V_{CEO} 100/120V, High current 1A.

 \cdot Low saturation voltage, excellent h_{FE} linearity.

Package Dimensions

unit:mm



(): 2SB631, 631K

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	2SB631, D600	2SB631K, D600K	Unit
Collector-to-Base Voltage	VCBO		(-)100	(–)120	V
Collector-to-Emitter Voltage	VCEO		(–)100	(–)120	V
Emitter-to-Base Voltage	V _{EBO}			(–)5	V
Collector Current	۱ _C			(–)1	A
Collector Current (Pulse)	ICP			(–)2	A
Collector Dissipation	PC				W
		Tc=25°C		8	W
Junction Temperature	Tj			150	°C
Storage Temperature	Tstg			-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions		Ratings			Unit
Falanielei	Symbol			min	typ	max	Onit
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =(-)10μA, I _E =0	B631, D600	(–)100			V
			B631K, D600K	(–)120			V
Collector-to-Emitter Brakdown Voltage	V _(BR) CEO	I _C =(–)1mA, R _{BE} =∞	B631, D600	(–)100			V
			B631K, D600K	(–)120			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =(–)10μΑ, I _C =0		(–)5			V
Collector Cutoff Current	ICBO	V _{CB} =(-)50V, I _E =0				(–)1	μΑ
Emitter Cutoff Current	I _{EBO}	V _{EB} =(-)4V, I _C =0				(–)1	μΑ

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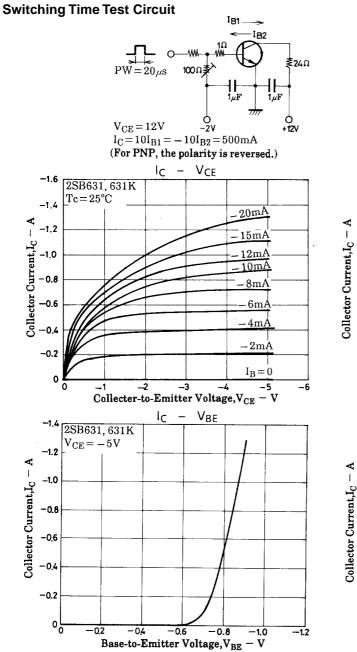
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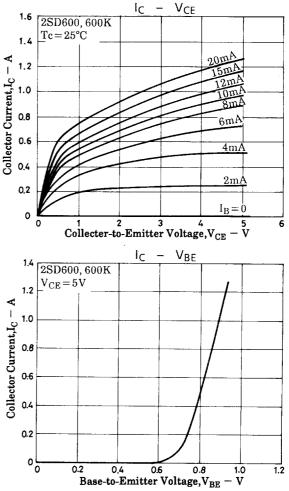
2SB631, 631K/2SD600, 600K

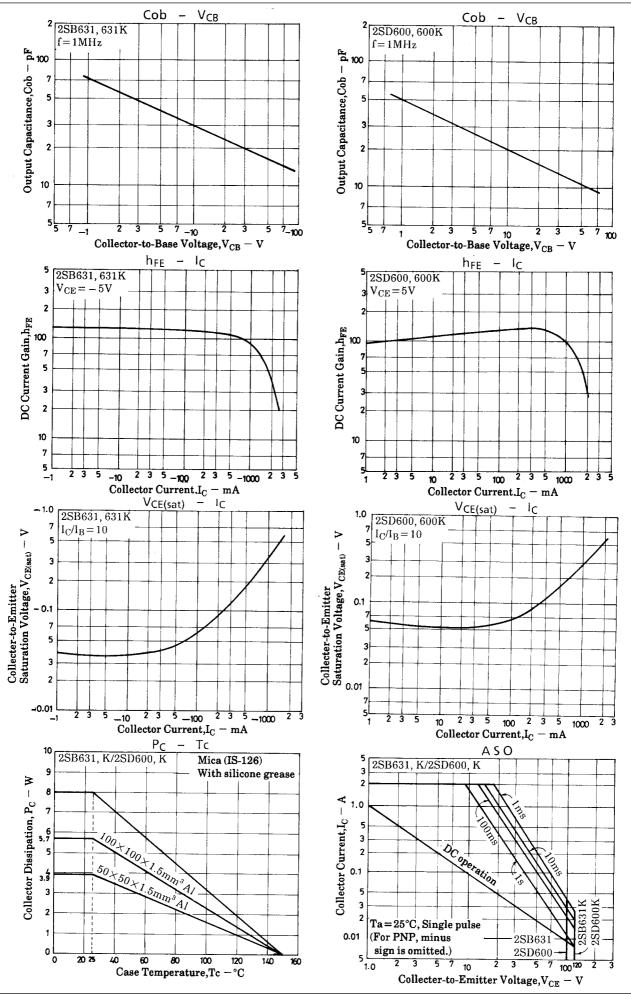
Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
DC Current Gain	h _{FE} 1	V _{CE} =(-)5V, I _C =(-)50mA	60*		320*	
	h _{FE} 2	V _{CE} =(-)5V, I _C =(-)500mA	20			
Gain-Bandwidth Product	fT	V _{CE} =(-)10V, I _C =(-)50mA		(110)		MHz
				130		MHz
Output Capacitance	C _{ob}	V _{CB} =(-)10V, f=1MHz		(30)20		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =(-)500mA, I _B =(-)50mA		(–)0.15	(–)0.4	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =(-)500mA, I _B =(-)50mA		(–)0.85	(–)1.2	V
Fall Time	t _f	See specified Test Circuit		(80)		ns
				100		ns
Turn-OFF Time	toff	See specified Test Circuit		(100)		ns
				500		ns
Storage Time	t _{stg}	See specified Test Circuit		(600)		ns
				700		ns

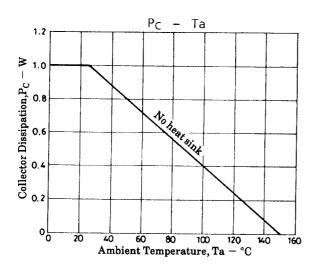
 \ast : The 2SB631/2SD600 are classified by 50mA h_{FE} as follows :











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